3.3 V LVTTL/LVCMOS to Differential LVPECL Translator

Description

The MC100LVELT20 is a 3.3 V TTL/CMOS to differential PECL translator. Because PECL (Positive ECL) levels are used, only + 3.3 V and ground are required. The small outline SOIC-8 package and the single gate of the MC100LVELT20 makes it ideal for those applications where space, performance, and low power are at a premium.

The 100 Series contains temperature compensation.

Features

- 390 ps Typical Propagation Delay
- Maximum Input Clock Frequency > 0.8 GHz Typical
- Operating Range $V_{CC} = 3.0 \text{ V}$ to 3.6 V with GND = 0 V
- PNP TTL Input for Minimal Loading
- Q Output will Default HIGH with Input Open
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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SOIC-8 NB D SUFFIX CASE 751-07

MARKING DIAGRAM



= Assembly	Locatior
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= Wafer Lot

А

L Y

w

= Year

= Work Week

= Pb-Free Package

*For additional marking information, refer to Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC100LVELT20DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC100LVELT20DR2G	SOIC-8 NB (Pb-Free)	2500/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

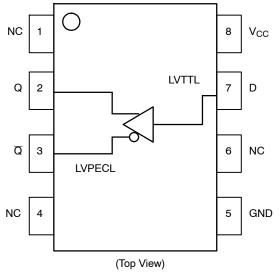


Table 1. PIN DESCRIPTION

Pin	Function
Q, <u>Q</u>	Differential PECL Outputs
D	LVTTL Input
V _{CC}	Positive Supply
GND	Ground
NC	No Connect

Figure 1. 8-Lead Pinout and Logic Diagram

Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 1.5 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	150 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	Power Supply	GND = 0 V		6	V
VI	Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	6	V
I _{out}	Output Current	Continuous Surge		50 100	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			–65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
T _{sol}	Wave Solder (Pb-Free)			265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Symbol	Characteristic	Min	Тур	Max	Unit
I _{IH}	Input HIGH Current (V _{in} = 2.7 V)			20	μA
I _{IHH}	Input HIGH Current MAX (V _{in} = 6.0 V)			100	μΑ
IIL	Input LOW Current (V _{in} = 0.5 V)			-0.6	mA
VIK	Input Clamp Voltage (I _{in} = -18 mA)			-1.2	V
VIH	Input HIGH Voltage	2.0			V
VIL	Input LOW Voltage			0.8	V

Table 4. LVTTL INPUT DC CHARACTERISTICS ($V_{CC} = 3.3 \text{ V}$, GND = 0 V, $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$)

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 5. 100LVELT PECL OUTPUT DC CHARACTERISTICS (V_{CC} = 3.3 V, GND = 0 V (Note 1))

		-40°C		25°C							
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Icc	Negative Power Supply Current	20	25	30	22	27	32	23	28	33	mA
V _{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Output parameters vary 1:1 with V_{CC} .

2. All loading with 50 Ω to V_{CC} – 2.0 V.

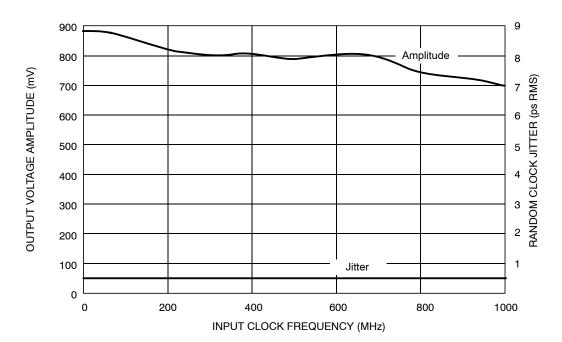
Table 6. AC CHARACTERISTICS (V_{CC} = 3.0 V to 3.6 V, GND = 0 V (Note 1))

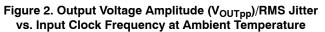
		-40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Input Clock Frequency (Figure 2)		800		600	800		600	800		MHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential	280	350	430	300	370	450	320	400	490	ps
t _{SKEW}	Device-to-Device Skew (Note 2)			250			250			250	ps
t _{JITTER}	Random Clock Jitter (RMS) (Figure 2)		< 1	< 2		< 1	< 2		< 1	< 2	ps
t _r t _f	Output Rise/Fall Times Q, Q (20% - 80%)	70	100	225	80	120	225	90	140	225	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Measured using a LVTTL source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

2. Skew is measured between outputs under identical transitions.





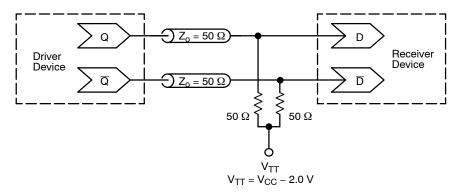


Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices.)

Resource Reference of Application Notes

AN1405/D	-	ECL Clock Distribution Techniques
AN1406/D	-	Designing with PECL (ECL at +5.0 V)
AN1503/D	-	ECLinPS [™] I/O SPiCE Modeling Kit
AN1504/D	-	Metastability and the ECLinPS Family
AN1568/D	-	Interfacing Between LVDS and ECL
AN1672/D	-	The ECL Translator Guide
AND8001/D	-	Odd Number Counters Design
AND8002/D	-	Marking and Date Codes
AND8020/D	-	Termination of ECL Logic Devices
AND8066/D	-	Interfacing with ECLinPS
AND8090/D	_	AC Characteristics of ECL Devices

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR З. 4. EMITTER EMITTER 5. BASE 6. 7 BASE 8. EMITTER STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. 5. GATE 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6. BASE, DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. 4. TXE 5. RXE 6. VFF GND 7. 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 З. CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C З. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. EMITTER, #1 BASE, #2 2. З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 З. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND BIAS 2 INPUT 6. 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. 5. P-DRAIN 6. P-DRAIN N-DRAIN 7. 8. N-DRAIN STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC I/O LINE 3 4. 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt ENABLE З. 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: PIN 1. DRAIN 1 DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1
STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd
STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1
STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON
STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1
STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT
STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN

DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER З. COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE CATHODE COLLECTOR/ANODE 6. 7. COLLECTOR/ANODE 8. STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET 3. 4. GND 5. 6. V MON VBULK 7. VBULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

8

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COLLECTOR, #1

COLLECTOR, #1